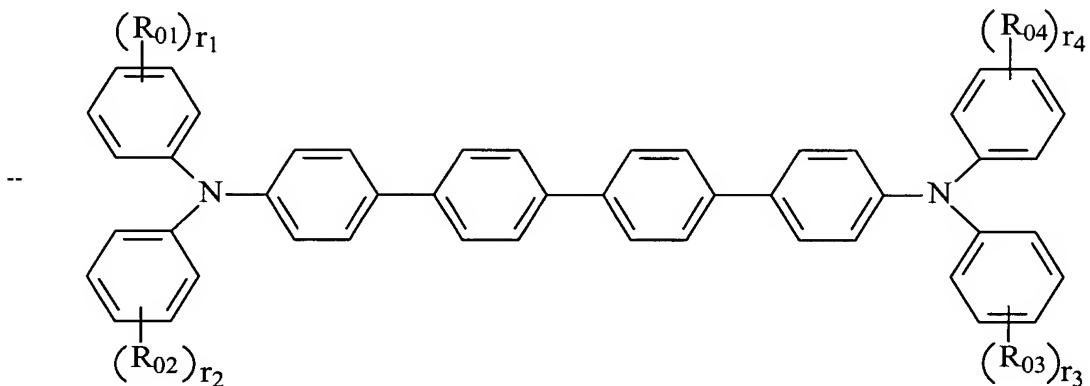


IN THE SPECIFICATION

Please delete the paragraph at page 7, lines 1-3.

Page 11, please replace formula (VI) with the following new formula (VI):



Please amend the paragraph at page 98, lines 1-24 as follows:

By using the compounds of the invention, the Hole mobility is so improved that a device having an increased current density can be obtained. The Hole mobility obtained by the compound of the invention is preferably at least $1.0 \times 10^{-3} \text{ cm}^2/\text{Vs}$, especially 1.1×10^{-3} to $100 \times 10^{-3} \text{ cm}^2/\text{Vs}$, and more especially 1.1×10^{-3} to $20.0 \times 10^{-3} \text{ cm}^2/\text{Vs}$. ~~The Hole mobility of the layer containing the compound of the invention is preferably up to 1/2, especially about 1/4 to 1/1,000, and more especially about 1/4 to 1/100 of that of the light emitting layer.~~ In the invention, the hole injecting layer is formed of the compound of the invention which imparts such excellent Hole mobility thereto. Even when such a hole injecting layer has a thickness of at least 100 nm, and especially at least 200 nm, there is obtained a device that can be operated with no difficulty. It is here to be noted that the upper limit on the thickness of the hole injecting layer is usually about 5,000 nm although the invention is not limited thereto. In the practice of the invention, this film thickness may be determined in such a

manner that, while the optical refractive index of each layer is taken into account, the optimum light extraction efficiency is obtained with no problem in conjunction with the angle of view, etc.

Please amend the paragraph at page 121, prenumbered lines 30-34 as follows:

N,N,N',N'-tetrakisbis-(3-biphenyl-1-yl)benzidine (TDP) having such a structure as given below and rubrene were co-evaporated at a weight ratio of 10:1 and a deposition rate of 0.2 nm/sec. to a thickness of 20 nm to form [[a]] an emitting hole transporting layer.

Please amend the paragraph at page 126, prenumbered lines 3-13 as follows:

A device was prepared as in example 1. Instead of the emitting hole transporting layer of example 1, however, [[a]] an emitting hole transporting and light emitting layer was formed by mixing a hole transporting material TPD, rubrene, i.e., a light emitting material having such a structure as given below and aluminum quinolinol (Alq^3), i.e., an electron injecting material having such a structure as given below at a weight mixing ratio of 5:5:1 to form a mixed layer of 40 nm in thickness by means of triple co-evaporation. Thereafter, aluminum quinolinol (Alq^3) was evaporated to a thickness of 30 nm.

Please amend the paragraph at page 127, prenumbered lines 12-17 as follows:

The emitting hole transporting layer of example 1 was formed of TPD alone, the thickness of the Alq^3 light emitting layer was changed to 10 nm, and a tetraphenylethene or phenylanthracene layer of 30 nm in thickness was interleaved between the hole transporting layer and the light emitting layer. Consequently, equivalent results as mentioned above were obtained.